40/588775 AP11 Rec'd PCT/PTO 08 AUG DANG 08 A& B (08-0)

4 h	IAP11 Rec'N PCT/PTO US AUTED/INTER/OS A & B (OS			
Substitute for Form 1449 A & B/PTO	Complete if Known			
Substitute for Form 1449 A & B/PTO	Application Number Not assigned 10/58877			
INFORMATION DISCLOSURE	Confirmation Number Not assigned yet			
STATEMENT BY APPLICANT	Filing Date August 8, 2006			
STATEMENT BY AFFLICANT	First Named Inventor Yasuhiro OKAMOTO			
(use as many sheets as necessary)	Art Unit Not assigned yet 2811			
	Examiner Name Not assigned yet Meiya L			
Sheet 1 of 1	Attorney Docket Number Q96219			

			U.S. 1	PATENT DOCUME	CNTS
Examiner Initials*	Cite No. <sup>1</sup>	Document	Document Number		
		Number	Kind Code <sup>2</sup> (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Documen
		US			

	Cite	Foreign Patent Document			Publication Date	Name of Patentee or	
Examiner Cite Initials* No.		Country Code <sup>3</sup>	Number <sup>4</sup>	Kind Code <sup>5</sup> (if known)	MM-DD-YYYY	Applicant of Cited Document	Translation
/M.L./		JP	2000-100831	Α	04-07-2000		
		JP	2001-308110	Α	11-02-2001		
		JP	2004-022773	A T	01-22-2004		
		JP	2003-273130	Α	09-26-2003		
		JP	07-321126	Α	12-08-1995		
7/		JР	04-154171	Α	05-27-1992		
V		JP	56-088364	Α	07-17-1981		
		- II	2744126	B	-03-06-1998		
						the state of the s	
		ii					

		NON PATENT LITERATURE DOCUMENTS	
Examiner Initials*	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city, and/or country where published.	Translation
/M.L./		J. Li et al. "High Breakdown Voltage GaN HFET with field plate" Electronics Letters, February 1, 2001, Vol. 37 No. 3 p. 196-197.	
			1

Examiner Signature	/Meiya Li/	Date Considered	12/10/2007

<sup>\*</sup>EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

<sup>&#</sup>x27;Applicant's unique citation designation number (optional). <sup>2</sup>See Kind Codes of USPTO Patent Documents at www.uspto.gov, MPEP 901.04 or follow the hyperlink from the title of the document to the intranet. <sup>3</sup> Enter Office that issued the document, by the two-letter code (WIPO Standard ST. 3). <sup>4</sup>For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. <sup>3</sup>Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. <sup>6</sup> Applicant is to indicate here if English language Translation is attached.